A Method of Wafer Smoothing for Bonding using Chemo-Mechanical Polishing (CMP)

Abstract

A method and apparatus is described incorporating a semiconductor substrate, CMP tool, a brush cleaning tool, and a chemical wafer cleaning tool The CMP is performed with a down force of 1 psi, a backside air pressure of 0.5 psi, a platen speed of 50 rpm, a carrier speed of 30 rpm and a slurry flow rate of 140 milliliters per minute.

Fig. 1

This Sheet Has Been Replaced

